

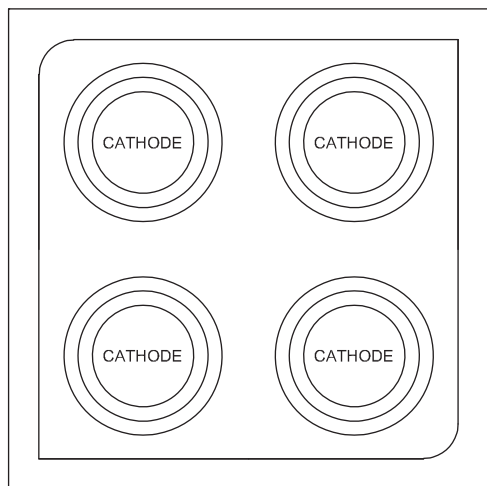
**PROCESS CPZ33R**  
**Transient Voltage Suppressor**  
**12 Volt Quad TVS Chip**



**PROCESS DETAILS**

Die Size	14.2 x 14.2 MILS
Die Thickness	3.9 MILS
Cathode Bonding Pad Areas (4)	4.7 MILS DIAMETER EACH
Top Side Metalization	Al - 13,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE ANODE R0

**GROSS DIE PER 5 INCH WAFER**

84,926

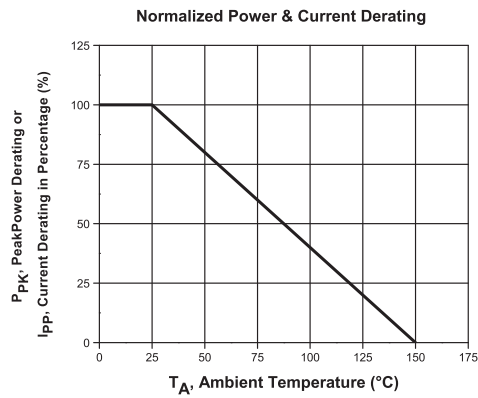
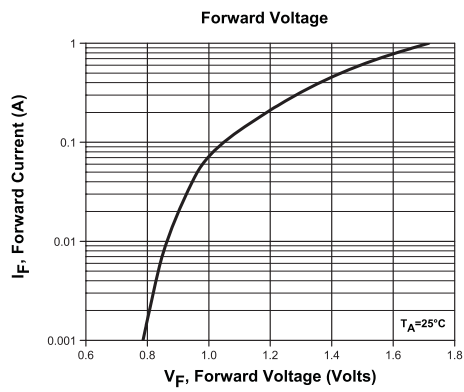
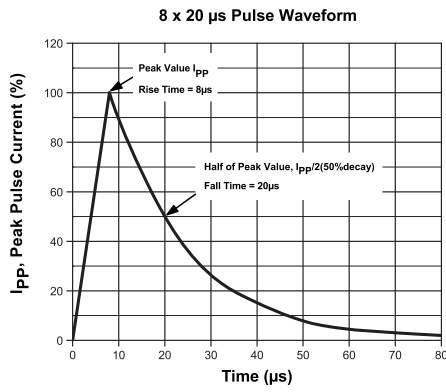
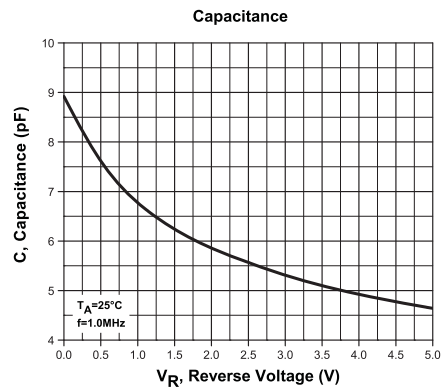
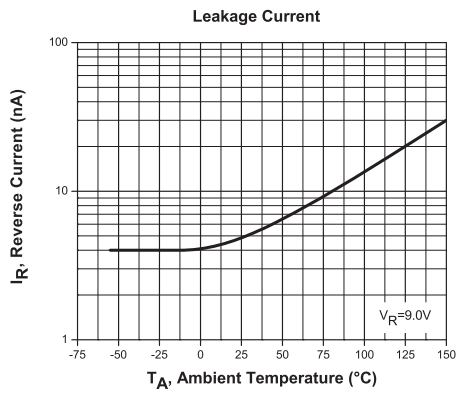
**PRINCIPAL DEVICE TYPE**

CMNTVS12V

R0 (3-January 2012)

# PROCESS CPZ33R

## Typical Electrical Characteristics



R0 (3-January 2012)